

**Homework J4**

In a linearly-graded junction, the doping varies linearly from one constant value on the  $n$ -side to another constant value on the  $p$ -side. This is essentially case (b) from Problem J2. Consider a linearly-graded junction made with GaAs. The graded region extends from an  $n$ -type doping level of  $N_D = 5 \times 10^{16} \text{ cm}^{-3}$  to a  $p$ -type level of  $N_A = 5 \times 10^{16} \text{ cm}^{-3}$ . The intrinsic region that is  $0.5\text{-}\mu\text{m}$  wide.

First sketch the band diagram, charge density profile, and electric profile at equilibrium. Then calculate the following,

The key to the problem is to assume that the graded layer will be completely depleted. Use your sketches to help with the calculations.

$$\phi_{bi} = \underline{\hspace{10cm}}$$

$$\mathcal{E}_{max} = \underline{\hspace{10cm}}$$

$$C_j = \underline{\hspace{10cm}}$$

$$J_{NS} = \underline{\hspace{10cm}}$$

$$J_{NP} = \underline{\hspace{10cm}}$$